

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China









Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at www.onsemi.com

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA Class 3 medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, emplo



January 2012

Motion-SPM ™

FSB50250AB

Smart Power Module (SPM®)

Features

- 500V $R_{DS(on)}$ =3.8 Ω (max) 3-phase FRFET inverter including high voltage integrated circuit (HVIC)
- 3 divided negative dc-link terminals for inverter current sensing applications
- · HVIC for gate driving and undervoltage protection
- 3/5V CMOS/TTL compatible, active-high interface
- · Optimized for low electromagnetic interference
- · Isolation voltage rating of 1500Vrms for 1min.
- · HVIC temperature sensing
- · Embedded bootstrap diode in the package
- · RoHS compliant



Applications

• Three-phase inverter driver for small power ac motor drives

General Description

FSB50250AB is a tiny smart power module (SPM®) based on FRFET technology as a compact inverter solution for small power motor drive applications such as fan motors and water suppliers. It is composed of 6 fast-recovery MOSFET (FRFET), and 3 half-bridge HVICs for FRFET gate driving. FSB50250AB provides low electromagnetic interference (EMI) characteristics with optimized switching speed. Moreover, since it employs FRFET as a power switch, it has much better ruggedness and larger safe operation area (SOA) than that of an IGBT-based power module or one-chip solution. The package is optimized for the thermal performance and compactness for the use in the built-in motor application and any other application where the assembly space is concerned. FSB50250AB is the best solution for the compact inverter providing the energy efficiency, compactness, and low electromagnetic interference.



Absolute Maximum Ratings

Inverter Part (Each FRFET Unless Otherwise Specified)

Symbol	Parameter	Conditions	Rating	Units
V _{PN}	DC Link Input Voltage, Drain-source Voltage of each FRFET		500	V
*I _{D25}	Each FRFET Drain Current, Continuous	T _C = 25°C	1.2	Α
*I _{D80}	Each FRFET Drain Current, Continuous	T _C = 80°C	0.9	Α
*I _{DP}	Each FRFET Drain Current, Peak	T _C = 25°C, PW < 100μs	3.1	Α
*I _{DRMS}	Each FRFET Drain Current, Rms	$T_C = 80^{\circ}C$, $F_{PWM} < 20KHz$	0.6	A _{rms}
*P _D	Maximum Power Dissipation	T _C = 25°C, For Each FRFET	13.4	W

Control Part (Each HVIC Unless Otherwise Specified)

Symbol	Parameter	Conditions	Rating	Units
V _{CC}	Control Supply Voltage	Applied between V _{CC} and COM	20	V
V _{BS}	High-side Bias Voltage	Applied between V_B and V_S	20	V
V_{IN}	Input Signal Voltage	Applied between IN and COM	-0.3 ~ V _{CC} +0.3	V

Bootstrap Diode Part (Each Bootstrap diode Unless Otherwise Specified)

Symbol	Parameter	r Conditions		Units
V_{RRMB}	Maixmum Repetitive Reverse Voltage		500	V
* I _{FB}	Forward Current	T _C = 25°C	0.5	Α
* I _{FPB}	Forward Current (Peak)	T _C = 25°C, Under 1ms Pulse Width	1.5	А

Thermal Resistance

Symbol	Parameter	Conditions	Rating	Units
$R_{ hetaJC}$	Lillingtion to Case Thermal Resistance	Each FRFET under inverter operating condition (Note 1)	9.3	°C/W

Total System

Symbol	Parameter	Conditions	Rating	Units
T _J	Operating Junction Temperature		-40 ~ 150	°C
T _{STG}	Storage Temperature		-40 ~ 125	°C
V _{ISO}	Isolation Voltage	60Hz, Sinusoidal, 1 minute, Connection pins to heatsink	1500	V_{rms}

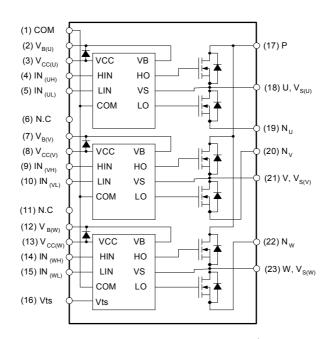
Note:

1. For the measurement point of case temperature $T_{\mbox{\scriptsize C}}$, please refer to Figure 4.

2. Marking " * " is calculation value or design factor.

Pin descriptions

Pin Number	Pin Name	Pin Description	
1	СОМ	IC Common Supply Ground	
2	V _{B(U)}	Bias Voltage for U Phase High Side FRFET Driving	
3	V _{CC(U)}	Bias Voltage for U Phase IC and Low Side FRFET Driving	
4	IN _(UH)	Signal Input for U Phase High-side	
5	IN _(UL)	Signal Input for U Phase Low-side	
6	N.C	N.C	
7	V _{B(V)}	Bias Voltage for V Phase High Side FRFET Driving	
8	V _{CC(V)}	Bias Voltage for V Phase IC and Low Side FRFET Driving	
9	IN _(VH)	Signal Input for V Phase High-side	
10	IN _(VL)	Signal Input for V Phase Low-side	
11	N.C	N.C	
12	V _{B(W)}	Bias Voltage for W Phase High Side FRFET Driving	
13	V _{CC(W)}	Bias Voltage for W Phase IC and Low Side FRFET Driving	
14	IN _(WH)	Signal Input for W Phase High-side	
15	IN _(WL)	Signal Input for W Phase Low-side	
16	V _{ts}	Output for HVIC temperature sensing	
17	Р	Positive DC–Link Input	
18	U, V _{S(U)}	Output for U Phase & Bias Voltage Ground for High Side FRFET Driving	
19	N _U	Negative DC-Link Input for U Phase	
20	N _V	Negative DC-Link Input for V Phase	
21	V, V _{S(V)}	Output for V Phase & Bias Voltage Ground for High Side FRFET Driving	
22	N _W	Negative DC–Link Input for W Phase	
23	W, V _{S(W)}	Output for W Phase & Bias Voltage Ground for High Side FRFET Driving	



Note:

Source terminal of each low-side MOSFET is not connected to supply ground or bias voltage ground inside SPM®. External connections should be made as indicated in Figure 3

Figure 1. Pin Configuration and Internal Block Diagram (Bottom View)

$\textbf{Electrical Characteristics} \ \, (\text{T}_{\text{J}} = 25^{\circ}\text{C}, \, \text{V}_{\text{CC}} = \text{V}_{\text{BS}} = 15\text{V Unless Otherwise Specified})$

Inverter Part (Each FRFET Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{IN} = 0V, I _D = 1mA (Note 1)	500	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{IN} = 0V, V _{DS} = 500V		-	1	mA
R _{DS(on)}	Static Drain-Source On-Resistance	V _{CC} = V _{BS} = 15V, V _{IN} = 5V, I _D = 0.5A		2.5	3.8	Ω
V _{SD}	Drain-Source Diode Forward Voltage	$V_{CC} = V_{BS} = 15V, V_{IN} = 0V, I_{D} = -0.5A$	-	-	1.2	٧
t _{ON}			-	1150	-	ns
t _{OFF}		V_{PN} = 300V, V_{CC} = V_{BS} = 15V, I_{D} = 0.5A	-	950	-	ns
t _{rr}	Switching Times	V _{IN} = 0V ↔ 5V, Inductive load L=3mH High- and low-side FRFET switching	-	190	-	ns
E _{ON}		(Note 2)	-	40	-	μJ
E _{OFF}				10	-	μJ
RBSOA	Reverse-bias Safe Operating Area	er- V_{PN} = 400V, V_{CC} = V_{BS} = 15V, I_D = I_{DP} , V_{DS} =BV _{DSS} , T_J = 150°C Full High- and low-side FRFET switching (Note 3)		Square		

Control Part (Each HVIC Unless Otherwise Specified)

Symbol	Parameter		Conditions	Min	Тур	Max	Units
I _{QCC}	Quiescent V _{CC} Current	V _{CC} =15V, V _{IN} =0V	Applied between V _{CC} and COM	-	-	200	μΑ
I _{QBS}	Quiescent V _{BS} Current	V _{BS} =15V, V _{IN} =0V	Applied between $V_{B(U)}$ -U, $V_{B(V)}$ -V, $V_{B(W)}$ -W	-	-	100	μΑ
UV _{CCD}	Low-side Undervoltage	V _{CC} Undervoltage Protection Detection Level		7.4	8.0	9.4	V
UV _{CCR}	Protection (Figure 8)	V _{CC} Undervoltage I	Protection Reset Level	8.0	8.9	9.8	V
UV _{BSD}	High-side Undervoltage	V _{BS} Undervoltage Protection Detection Level		7.4	8.0	9.4	V
UV _{BSR}	Protection (Figure 9)	V _{BS} Undervoltage F	V _{BS} Undervoltage Protection Reset Level		8.9	9.8	V
V _{ts}	HVIC Temperature sens- ing voltage output	V _{CC} =15V, T _{HVIC} =25°C(Note 4)		600	790	980	mV
V _{IH}	ON Threshold Voltage	Logic High Level		2.9	-	-	V
V _{IL}	OFF Threshold Voltage	Logic Low Level	Applied between IN and COM		-	0.8	V

Bootstrap Diode Part (Each Bootstrap diode Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V_{FB}	Forward Voltage	I _F = 0.1A, T _C = 25°C(Note 5)	-	2.5	-	V
t _{rrB}	Reverse Recovery Time	$I_F = 0.1A, T_C = 25^{\circ}C$	-	80	-	ns

- 1. BV_{DSS} is the absolute maximum voltage rating between drain and source terminal of each FRFET inside SPM[®]. V_{PN} should be sufficiently less than this value considering the effect of the stray inductance so that V_{DS} should not exceed BV_{DSS} in any case.
- 2. t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. Listed values are measured at the laboratory test condition, and they can be different according to the field applications due to the effect of different printed circuit boards and wirings. Please see Figure 6 for the switching time definition with the switching test circuit of Figure 7.
- 3. The peak current and voltage of each FRFET during the switching operation should be included in the safe operating area (SOA). Please see Figure 7 for the RBSOA test circuit that is same as the switching test circuit.
- 4. V_{ts} is only for sensing temperature of module and cannot shutdown MOSFETs automatically.
- 5. Built in bootstrap diode includes around 15 Ω resistance characteristic. Please refer to Figure 2.

Recommended Operating Condition

Cumbal	Parameter	Conditions		Unito		
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
V _{PN}	Supply Voltage	Applied between P and N	-	300	400	V
V _{CC}	Control Supply Voltage	Applied between V _{CC} and COM	13.5	15	16.5	V
V _{BS}	High-side Bias Voltage	Applied between V _B and V _S	13.5	15	16.5	V
V _{IN(ON)}	Input ON Threshold Voltage	Applied between IN and COM	3.0	-	V _{CC}	V
V _{IN(OFF)}	Input OFF Threshold Voltage	Applied between IIV and Golvi	0	-	0.6	V
t _{dead}	Blanking Time for Preventing Arm-short	V _{CC} =V _{BS} =13.5 ~ 16.5V, T _J ≤ 150°C	1.0	-	-	μS
f _{PWM}	PWM Switching Frequency	$T_J \le 150$ °C	-	15	-	kHz

Package Marking & Ordering Information

Device Marking	Device	Package	Reel Size	Packing Type	Quantity
FSB50250AB	FSB50250AB	SPM23DD-21L	-	-	15

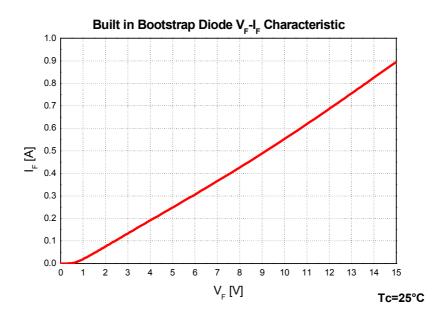
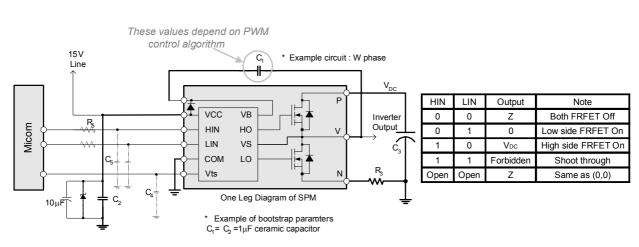


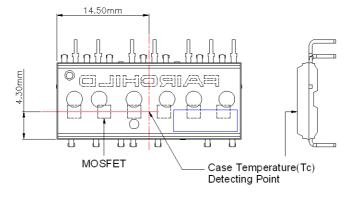
Figure 2. Built in Bootstrap Diode Characteristics(typ.)



Note:

- 1. Parameters for bootsrap circuit elements are dependent on PWM algorithm. For 15 kHz of switching frequency, typical example of parameters is shown above.
- RC coupling(R₅ and C₅) and C₄ at each input of SPM[®] and Micom (indicated as dotted lines) may be used to prevent improper signal due to surge noise. Signal input of SPM[®] is compatible with standard CMOS or LSTTL outputs.
- Bold lines should be short and thick in PCB pattern to have small stray inductance of circuit, which results in the reduction of surge voltage. Bypass capacitors such as C₁, C₂ and C₃ should have good high-frequencycharacteristics to absorb high-frequency ripple current.

Figure 3. Recommended CPU Interface and Bootstrap Circuit with Parameters



Note:

Attach the thermocouple on top of the heatsink-side of SPM® (between SPM® and heatsink if applied) to get the correct temperature measurement.

Figure 4. Case Temperature Measurement

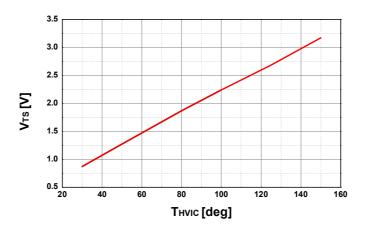
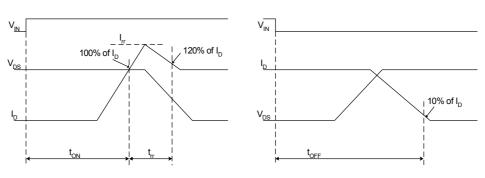


Figure 5. Temperature profile of Vts(typ.)



(a) Turn-on (b) Turn-off Figure 6. Switching Time Definition

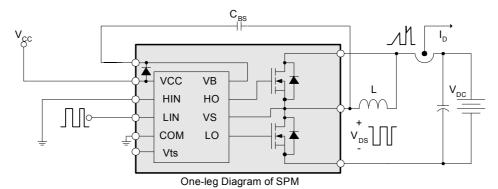


Figure 7. Switching and RBSOA(Single-pulse) Test Circuit (Low-side)

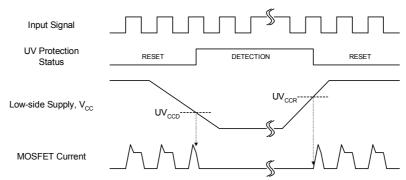


Figure 8. Undervoltage Protection (Low-side)

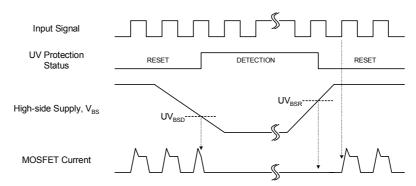
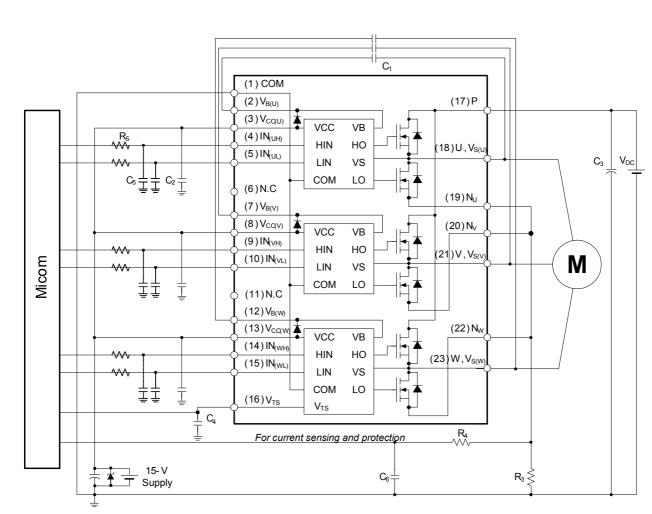


Figure 9. Undervoltage Protection (High-side)

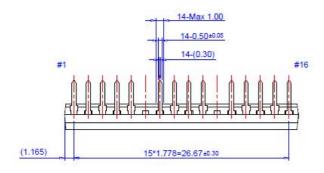


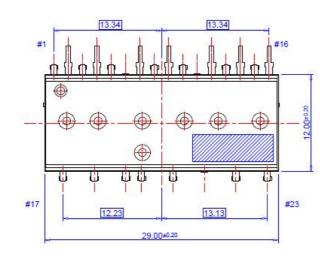
Note:

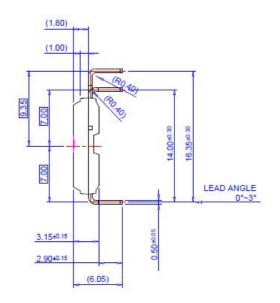
- 1. About pin position, refer to Figure 2.
- 2. RC coupling(R_5 and C_5 , R_4 and C_6) and C_4 at each input of SPM 8 and Micom are useful to prevent improper input signal caused by surge noise.
- 3. The voltage drop across R₃ affects the low side switching performance and the bootstrap characteristics since it is placed between COM and the source terminal of the low side MOSFET. For this reason, the voltage drop across R₃ should be less than 1V in the steady-state.
- 4. Ground wires and output terminals, should be thick and short in order to avoid surge voltage and malfunction of HVIC.
- $5. \ All \ the \ filter \ capacitors \ should \ be \ connected \ close \ to \ SPM^{\textcircled{\tiny{8}}}, \ and \ they \ should \ have \ good \ characteristics \ for \ rejecting \ high-frequency \ ripple \ current.$

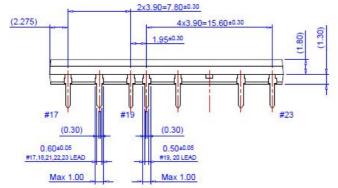
Figure 10. Example of Application Circuit

Detailed Package Outline Drawings









Dimension unit: [mm]





TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

Build it Now™ CorePLUS™ CorePOWER™ CROSSVOLT™

CTL™ Current Transfer Logic™

EcoSPARK® EfficentMax™ EZSWITCH™ *

-airchild®

Fairchild Semiconductor® FACT Quiet Series T

FAST® FastvCore™ FlashWriter® *

FPS™ F-PFS™

FRFET® Global Power ResourceSM Green FPS™

Green FPS™ e-Series™

GTO™ IntelliMAX™ ISOPLANAR™ MegaBuck™ MICROCOUPLER™

MicroFFT™ MicroPak™ MillerDrive™ MotionMax™ Motion-SPM™ OPTOLOGIC® OPTOPLANAR®

PDP SPM™

Power-SPM™ PowerTrench® PowerXS™

Programmable Active Droop™

QFĔT QS™ Quiet Series™ RapidConfigure™

Saving our world, 1mW /W /kW at a time™ SmartMax™

SMART START™ SPM® STEALTH™ SuperFET™ SuperSOT™-3 SuperSOT™-6 SuperSOT™-8

SyncFET™ SYSTEM ® GENERAL

SupreMOS™

The Power Franchise®

puwer franchise TinyBoost™ TinyBuck™ TinyLogic[®]
TINYOPTO™ TinvPower™ TinyPWM™ TinyWire™ TriÉault Detect™

UHC® Ultra FRFET™ UniFET™ **VCX™** VisualMax™

XSTM

uSerDes™

* EZSWITCH™ and FlashWriter® are trademarks of System General Corporation, used under license by Fairchild Semiconductor.

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

EIPE SUPPORT FOLION.
FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.Fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufactures of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed application, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handing and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address and warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS **Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary First Production Datasheet contains preliminary data; supplementary data will be publishe date. Fairchild Semiconductor reserves the right to make changes at any notice to improve design.		Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed Full Production Datasheet contains final specifications. Fairchild Semiconductor reserves the rimake changes at any time without notice to improve the design.		Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I38

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and see no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and h

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Phone: 421 33 790 2910

Japan Customer Focus Center

Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative